LM613x Dual and Quad, Low-Power, 10MHz, Rail-to-Rail I/O Operational Amplifiers

1 Features

- (For 5V supply, typical unless noted)
- Rail-to-rail input CMVR: −0.25V to 5.25V
- Rail-to-rail output
- High gain-bandwidth: 10MHz at 20kHz
- Slew rate: 12V/µs
- Low supply current: 360µA/amp
- Wide supply range: 2.7V to over 24V
- CMRR: 100dB
- Gain: 100dB with R_L = 10kΩ
- PSRR: 82dB

2 Applications

- Battery-operated instrumentation
- Instrumentation amplifiers
- Portable scanners
- Wireless communications
- Flat-panel display driver

3 Description

The LM6132 and LM6134 (LM613x) provide new levels of speed versus power performance in applications where low-voltage supplies or power limitations previously made compromise necessary. With only 360µA/amp supply current, the 10MHz gain-bandwidth of this device supports new portable applications where higher power devices unacceptably drain battery life.

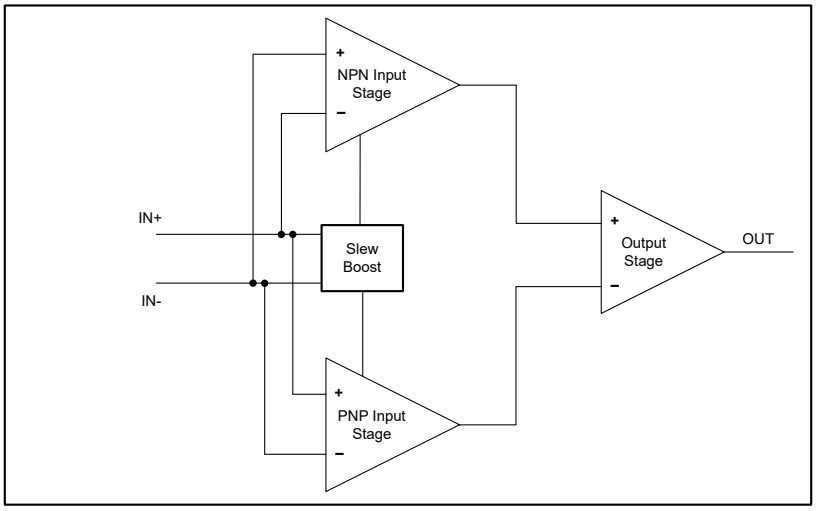
The LM613x can be driven by voltages that exceed both power supply rails, thus eliminating concerns over exceeding the common-mode voltage range. The rail-to-rail output swing capability provides the maximum possible dynamic range at the output. This feature is particularly important when operating on low supply voltages. The LM613x also drives large capacitive loads without oscillating.

Operating on supplies from 2.7V to over 24V, the LM6132x are excellent for a very wide range of applications, from battery-operated systems with large bandwidth requirements to high-speed instrumentation.

Device Information

PART NUMBER	CHANNEL COUNT	PACKAGE(1)	BODY SIZE
LM6132	Dual	D (SOIC, 8)	4.90mm × 3.91mm
		P (PDIP, 8)	9.81mm × 6.35mm
LM6134	Quad	D (SOIC, 14)	8.65mm × 3.91mm
		NFF (PDIP, 14)	19.177mm × 6.35mm

(1) For more information, see Section 9.



Functional Block Diagram

An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.

Table of Contents

1 Features....1
2 Applications....1
3 Description....1
4 Pin Configuration and Functions....3
5 Specifications....4
5.1 Absolute Maximum Ratings....4
5.2 ESD Ratings....4
5.3 Recommended Operating Conditions....4
5.4 Thermal Information LM6132....5
5.5 Thermal Information LM6134....5
5.6 Electrical Characteristics: V_S = 5V....6
5.7 Electrical Characteristics: V_S = 2.7V....8
5.8 Electrical Characteristics: V_S = 24V....9
5.9 Typical Characteristics....10
5.10 Old Versus New Die Comparison....15
6 Application and Implementation....16
6.1 Application Information....16
6.2 Typical Applications....17
7 Device and Documentation Support....18
7.1 Receiving Notification of Documentation Updates....18
7.2 Support Resources....18
7.3 Trademarks....18
7.4 Electrostatic Discharge Caution....18
7.5 Glossary....18
8 Revision History....18
9 Mechanical, Packaging, and Orderable Information....19

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4 Pin Configuration and Functions

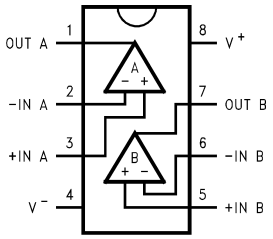


Figure 4-1. D Package, 8-Pin SOIC,and P Package, 8-Pin PDIP (Top View)

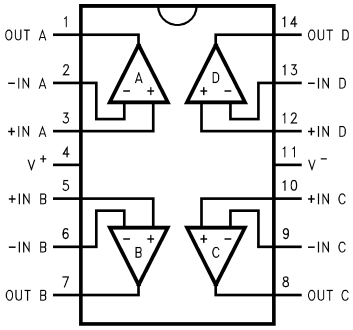


Figure 4-2. D Package, 14-Pin SOIC, and NFF Package, 14-Pin PDIP (Top View)

Pin Functions

PIN			TYPE	DESCRIPTION
NAME	LM6132	LM6134		
	D (SOIC), P (PDIP)	D (SOIC), NFF (PDIP)		
–IN A	2	2	Input	ChA inverting input
+IN A	3	3	Input	ChA noninverting input
–IN B	6	6	Input	ChB inverting input
+IN B	5	5	Input	ChB noninverting input
–IN C		9	Input	ChC inverting input
+IN C		10	Input	ChC noninverting input
–IN D		13	Input	ChD inverting input
+IN D		12	Input	ChD noninverting input
OUT A	1	1	Output	ChA output
OUT B	7	7	Output	ChB output
OUT C		8	Output	ChC output
OUT D		14	Output	ChD output
V^-	4	11	Input	Negative supply
V^+	8	4	Input	Positive supply

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5 Specifications

5.1 Absolute Maximum Ratings

over operating ambient temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
Supply voltage, V_S = (V+) – (V–)		0	33	V
Signal input pins	Common-mode voltage(3)	(V–) – 0.5	(V+) + 0.5	V
	Differential voltage(4)		±15	V
	Current(3)		±10	mA
Output short-circuit(2)		Continuous		
Operating ambient temperature, T_A		–55	150	°C
Junction temperature, T_J			150	°C
Storage temperature, T_{stg}		–65	150	°C

(1) Operating the device beyond the ratings listed under *Absolute Maximum Ratings* will cause permanent damage to the device. These are stress ratings only, based on process and design limitations, and this device has not been designed to function outside the conditions indicated under *Recommended Operating Conditions*. Exposure to any condition outside *Recommended Operating Conditions* for extended periods, including absolute-maximum-rated conditions, may affect device reliability and performance.
(2) Short-circuit to ground, one amplifier per package. Extended short-circuit current, especially with higher supply voltage, can cause excessive heating and eventual destruction.
(3) Input pins are diode-clamped to the power-supply rails. Input signals that may swing more than 0.5V beyond the supply rails must be current limited to 10mA or less.
(4) Input pins are connected by back-to-back diodes for input protection. If the differential input voltage may exceed 0.5V, limit the input current to 10mA or less.

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±4000	V
		Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002(2)	±1500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating ambient temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V_S	Supply voltage, (V+) – (V–)	2.7	24	V
V_I	Common mode voltage range	(V–) – 0.1	(V+) + 0.1	V
T_A	Specified temperature	–40	85	°C

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5.4 Thermal Information LM6132

THERMAL METRIC[1]		LM6132		UNIT
		D (SOIC)	P (PDIP)	
		8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	127.10	84.45	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	63.27	58.07	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	71.20	50.90	°C/W
ψ_{JT}	Junction-to-top characterization parameter	13.91	30.43	°C/W
ψ_{JB}	Junction-to-board characterization parameter	70.54	50.44	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, SPRA953.

5.5 Thermal Information LM6134

THERMAL METRIC[1]		LM6134		Unit
		D (SOIC)	NFF (PDIP)	
		14 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	82.48	81	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	38.77	N/A	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	37.86	N/A	°C/W
ψ_{JT}	Junction-to-top characterization parameter	8.66	N/A	°C/W
ψ_{JB}	Junction-to-board characterization parameter	37.51	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, SPRA953.

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5.6 Electrical Characteristics: V_S = 5V

For V^+ = 5.0V, V^- = 0V, R_L > 1MΩ connected to V_S / 2, V_{CM} = V^+ / 2, and V_O = V^+ / 2, at T_A = 25°C, unless otherwise noted.

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
OFFSET VOLTAGE							
V_{OS}	Input offset voltage	LM6132AI, LM6134AI			0.25	2	mV
			T_A = –40°C to 85°C			4	
		LM6132BI, LM6134BI			0.25	6	
			T_A = –40°C to 85°C			8	
dV_{OS}/dT	Input offset voltage drift	T_A = –40°C to 85°C			5		µV/°C
PSRR	Input offset voltage versus power supply	2.5V ≤ $\|V_S\|$ ≤ 12V, LM6132AI, LM6134AI		78	82		dB
			T_A = –40°C to 85°C	75			
		2.5V ≤ $\|V_S\|$ ≤ 12V, LM6132BI, LM6134BI		78	82		
			T_A = –40°C to 85°C	75			
INPUT BIAS CURRENT							
I_B	Input bias current	0V ≤ V_{CM} ≤ 5V, LM6132AI, LM6134AI			110	140	nA
			T_A = –40°C to 85°C			300	
		0V ≤ V_{CM} ≤ 5V, LM6132BI, LM6134BI			110	180	
			T_A = –40°C to 85°C			350	
I_{OS}	Input offset current	LM6132AI, LM6134AI			3.4	30	nA
			T_A = –40°C to 85°C			50	
		LM6132BI, LM6134BI			3.4	30	
			T_A = –40°C to 85°C			50	
INPUT VOLTAGE							
V_{CM}	Common-mode input voltage range			– 0.25		5.25	V
		T_A = –40°C to 85°C		0		5	V
CMRR	Common-mode rejection ratio	0V ≤ V_{CM} ≤ 4V, LM6132AI, LM6134AI		75	100		dB
			T_A = –40°C to 85°C	70			
		0V ≤ V_{CM} ≤ 4V, LM6132BI, LM6134BI		75	100		
			T_A = –40°C to 85°C	70			
		0V ≤ V_{CM} ≤ 5V, LM6132AI, LM6134AI		60	100		
			T_A = –40°C to 85°C	55			
		0V ≤ V_{CM} ≤ 5V, LM6132BI, LM6134BI		60	100		
			T_A = –40°C to 85°C	55			
INPUT IMPEDANCE							
R_{IN}	Common-mode input resistance				104		MΩ
OPEN-LOOP GAIN							
A_{OL}	Open-loop voltage gain	R_L = 10kΩ, LM6132AI, LM6134AI		25	100		V/mV
			T_A = –40°C to 85°C	8			
		R_L = 10kΩ, LM6132BI, LM6134BI		15	100		
			T_A = –40°C to 85°C	6			
NOISE							
e_N	Input voltage noise density	f = 1kHz			27		nV/√Hz
i_N	Input current noise density	f = 1kHz			0.18		pA/√Hz
FREQUENCY RESPONSE							
GBW	Gain-bandwidth product	f = 20kHz		7.4	10		MHz
			T_A = –40°C to 85°C	7			
SR	Slew rate	V_S = 12V, V_{STEP} = 8V, R_S < 1kΩ		8	14		V/µs
			T_A = –40°C to 85°C	7			
PM	Phase margin	R_L = 10 kΩ			33		°
GM	Gain margin	R_L = 10 kΩ			10		dB

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For V^+ = 5.0V, V^- = 0V, R_L > 1MΩ connected to V_S / 2, V_{CM} = V^+ / 2, and V_O = V^+ / 2, at T_A = 25°C, unless otherwise noted.

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
OUTPUT							
V_O	Voltage output swing	R_L = 100kΩ, From positive rail			30	40	mV
			T_A = –40°C to 85°C			70	
		R_L = 100kΩ, From negative rail			30	35	
			T_A = –40°C to 85°C			50	
		R_L = 10kΩ, From positive rail			48	60	
			T_A = –40°C to 85°C			150	
		R_L = 10kΩ, From negative rail			32	70	
			T_A = –40°C to 85°C			90	
		R_L = 5kΩ, From positive rail			77	100	
			T_A = –40°C to 85°C			150	
		R_L = 5kΩ, From negative rail			51	95	
			T_A = –40°C to 85°C			120	
I_{SC}	Short-circuit current	Sourcing, LM6132A		2	4		mA
			T_A = –40°C to 85°C	2			
		Sourcing, LM6132B		2	4		
			T_A = –40°C to 85°C	1			
		Sinking, LM6132A		1.8	3.5		
			T_A = –40°C to 85°C	1.8			
		Sinking, LM6132B		1.8	3.5		
			T_A = –40°C to 85°C	1			
		Sourcing, LM6134A		2	3		
			T_A = –40°C to 85°C	1.6			
		Sourcing, LM6134B		2	3		
			T_A = –40°C to 85°C	1			
		Sinking, LM6134A		1.8	3.5		
			T_A = –40°C to 85°C	1.3			
		Sinking, LM6134B		1.8	3.5		
			T_A = –40°C to 85°C	1			
POWER SUPPLY							
I_Q	Quiescent current per amplifier	LM6132AI, LM6134AI			360	400	µA
			T_A = –40°C to 85°C			450	
		LM6132BI, LM6134BI			360	400	µA
			T_A = –40°C to 85°C			450	µA

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5.7 Electrical Characteristics: V_S = 2.7V

For V^+ = 2.7V, V^- = 0V, R_L > 1MΩ connected to V_S / 2, V_{CM} = V^+ / 2, and V_O = V^+ / 2, at T_A = 25°C, unless otherwise noted.

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
OFFSET VOLTAGE							
V_{OS}	Input offset voltage	LM6132AI, LM6134AI			0.12	2	mV
			T_A = –40°C to 85°C			8	
		LM6132BI, LM6134BI			0.12	6	
			T_A = –40°C to 85°C			12	
PSRR	Input offset voltage versus power supply	1.35V ≤ |V_S| ≤ 12V,			80		dB
INPUT BIAS CURRENT							
I_B	Input bias current	0V ≤ V_{CM} ≤ 2.7V			90		nA
I_{OS}	Input offset current				2.8		nA
INPUT VOLTAGE							
V_{CM}	Common-mode input voltage range			0		2.7	V
CMRR	Common-mode rejection ratio	0V ≤ V_{CM} ≤ 2.7V			82		dB
INPUT IMPEDANCE							
R_{IN}	Common-mode input resistance				134		MΩ
OPEN-LOOP GAIN							
A_{OL}	Open-loop voltage gain	R_L = 10kΩ			100		V/mV
NOISE							
FREQUENCY RESPONSE							
GBW	Gain-bandwidth product	f = 20kHz, R_L = 10 kΩ			7		MHz
PM	Phase margin	R_L = 10 kΩ			23		°
GM	Gain margin				12		dB
OUTPUT							
V_O	Voltage output swing	R_L = 100kΩ, From positive rail			40	50	mV
			T_A = –40°C to 85°C			450	
		R_L = 100kΩ, From negative rail			30	80	
			T_A = –40°C to 85°C			112	
POWER SUPPLY							
I_Q	Quiescent current per amplifier				330		µA

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5.8 Electrical Characteristics: V_S = 24V

For V^+ = 24V, V^- = 0V, R_L > 1MΩ connected to V_S / 2, V_{CM} = V^+ / 2, and V_O = V^+ / 2, at T_A = 25°C, unless otherwise noted.

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
OFFSET VOLTAGE							
V_{OS}	Input offset voltage	LM6132AI, LM6134AI			1.7	3	mV
			T_A = –40°C to 85°C			5	
		LM6132BI, LM6134BI			1.7	7	
			T_A = –40°C to 85°C			9	
PSRR	Input offset voltage versus power supply	1.35V ≤ |V_S| ≤ 12V,			82		dB
INPUT BIAS CURRENT							
I_B	Input bias current	0V ≤ V_{CM} ≤ 24V			125		nA
I_{OS}	Input offset current				4.8		nA
INPUT VOLTAGE							
V_{CM}	Common-mode input voltage range			0		24	V
CMRR	Common-mode rejection ratio	0V ≤ V_{CM} ≤ 24V			82		dB
INPUT IMPEDANCE							
R_{IN}	Common-mode input resistance				210		MΩ
OPEN-LOOP GAIN							
A_{OL}	Open-loop voltage gain	R_L = 10kΩ			102		V/mV
NOISE							
FREQUENCY RESPONSE							
GBW	Gain-bandwidth product	f = 20kHz, R_L = 10 kΩ			11		MHz
PM	Phase margin	R_L = 10 kΩ			23		°
GM	Gain margin	R_L = 10 kΩ			12		dB
THD+N	Total harmonic distortion + noise	V_O = 20V_{PP}, G = 1, f = 10kHz			0.0015		%
OUTPUT							
V_O	Voltage output swing	R_L = 10kΩ, From positive rail			140	200	mV
		R_L = 10kΩ, From negative rail			75	150	
POWER SUPPLY							
I_Q	Quiescent current per amplifier				390	450	µA
		T_A = –40°C to 85°C				490	

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5.9 Typical Characteristics

at T_A = 25°C and R_L = 10 kΩ (unless otherwise specified)

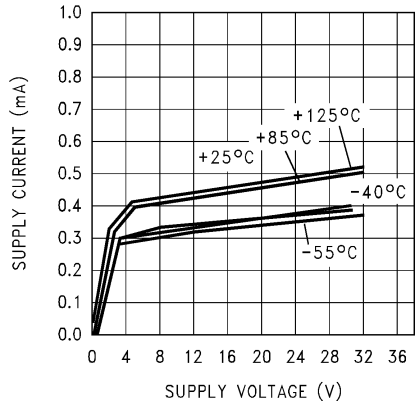


Figure 5-1. Supply Current vs Supply Voltage

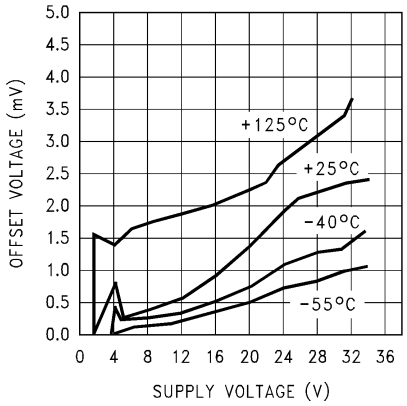


Figure 5-2. Offset Voltage vs Supply Voltage

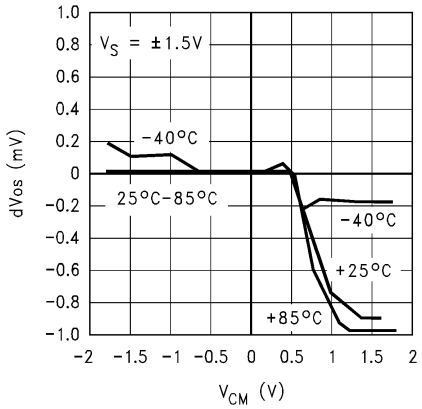


Figure 5-3. dV_{OS} vs V_{CM}

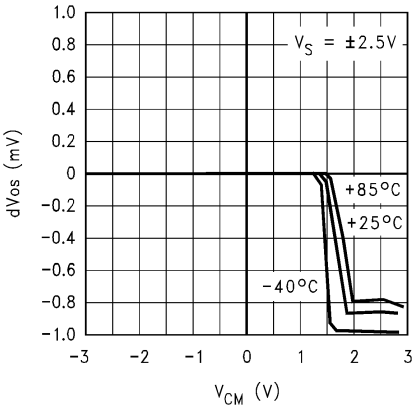


Figure 5-4. dV_{OS} vs V_{CM}

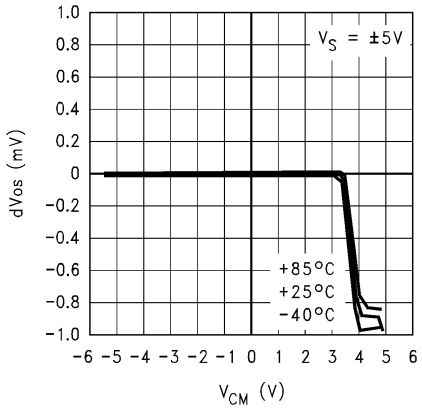


Figure 5-5. dV_{OS} vs V_{CM}

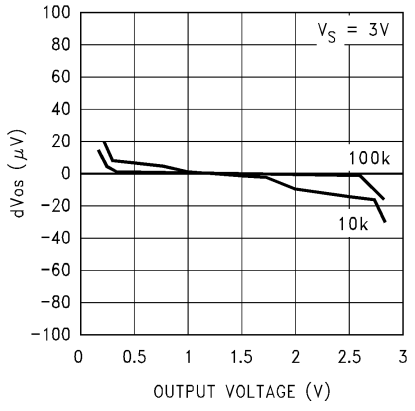


Figure 5-6. dV_{OS} vs Output Voltage

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5.9 Typical Characteristics (continued)

at T_A = 25°C and R_L = 10 kΩ (unless otherwise specified)

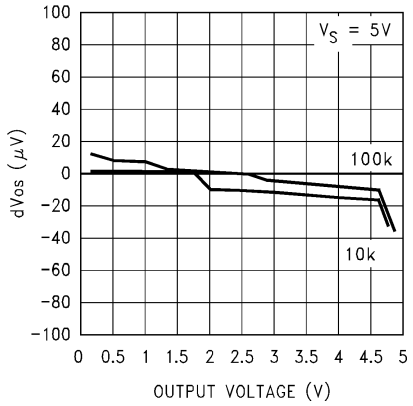


Figure 5-7. dV_{OS} vs Output Voltage

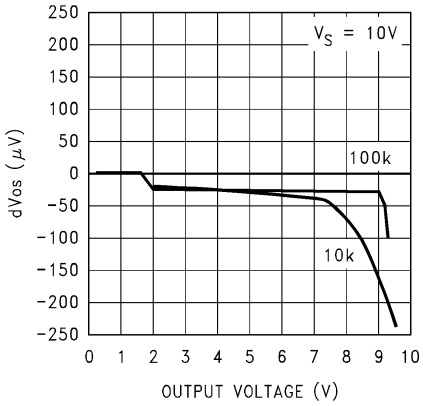


Figure 5-8. dV_{OS} vs Output Voltage

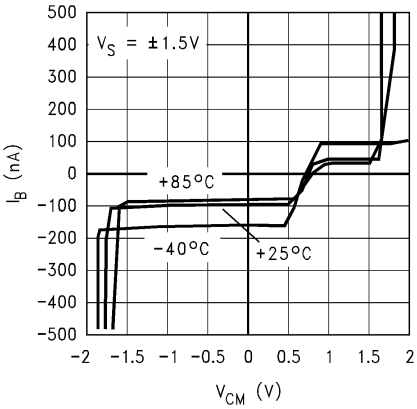


Figure 5-9. I_{BIAS} vs V_{CM}

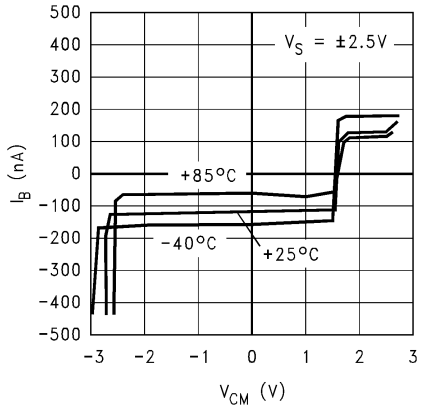


Figure 5-10. I_{BIAS} vs V_{CM}

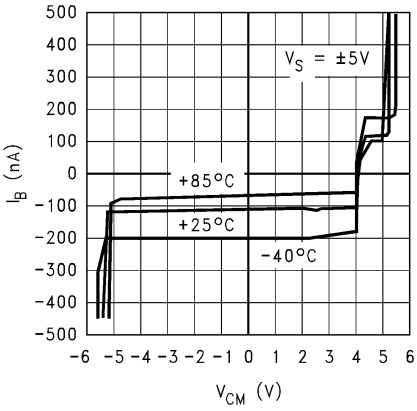


Figure 5-11. I_{BIAS} vs V_{CM}

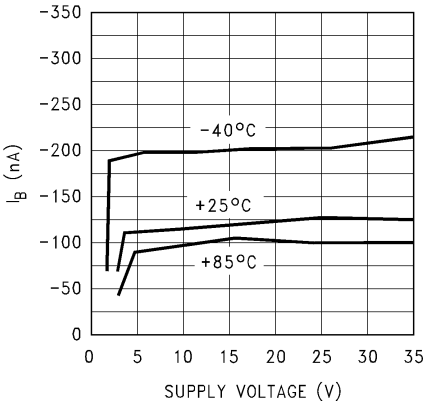


Figure 5-12. Input Bias Current vs Supply Voltage

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5.9 Typical Characteristics (continued)

at T_A = 25°C and R_L = 10 kΩ (unless otherwise specified)

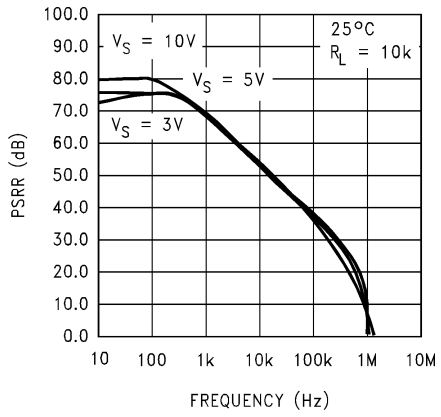


Figure 5-13. Negative PSRR vs Frequency, Old Die

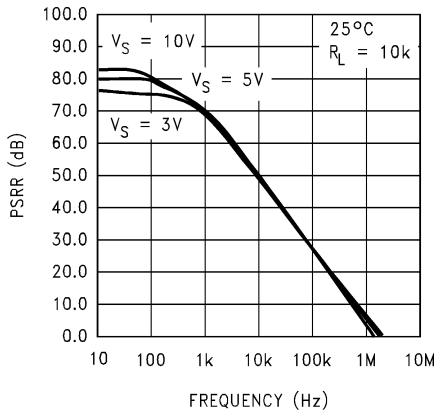


Figure 5-14. Positive PSSR vs Frequency, Old Die

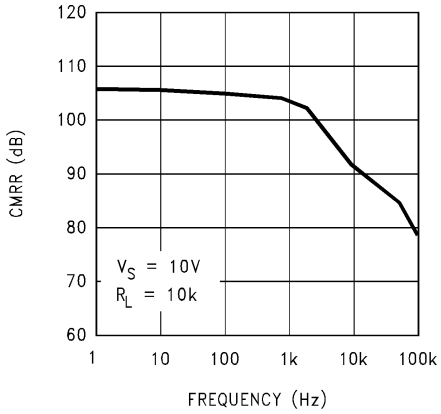


Figure 5-15. CMRR vs Frequency, Old Die

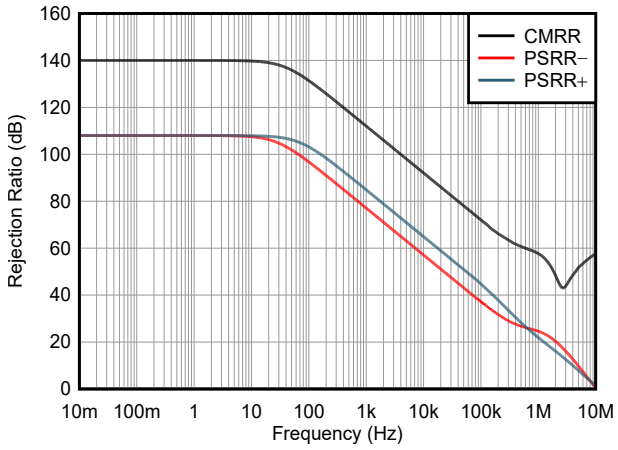


Figure 5-16. CMRR and PSRR vs Frequency, New Die

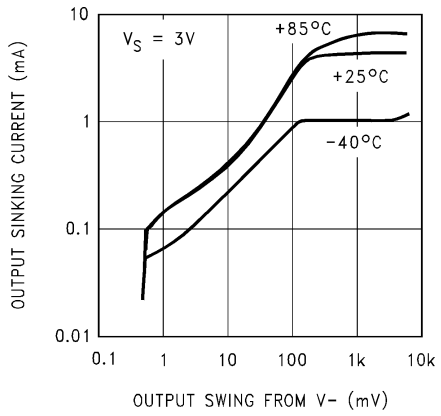


Figure 5-17. Output Voltage vs Sinking Current

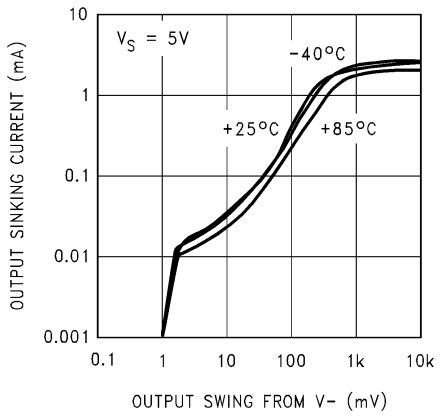


Figure 5-18. Output Voltage vs Sinking Current

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5.9 Typical Characteristics (continued)

at T_A = 25°C and R_L = 10 kΩ (unless otherwise specified)

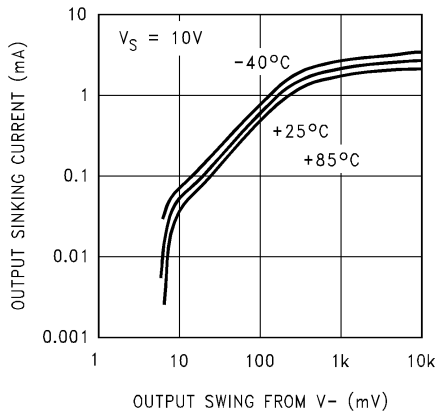


Figure 5-19. Output Voltage vs Sinking Current

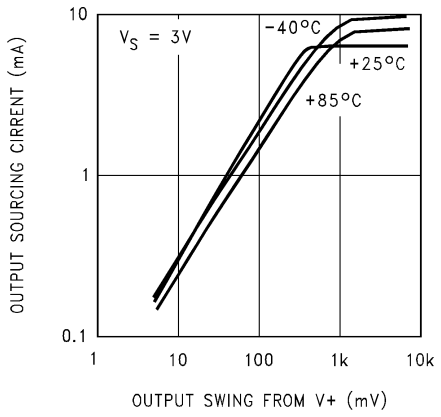


Figure 5-20. Output Voltage vs Sourcing Current

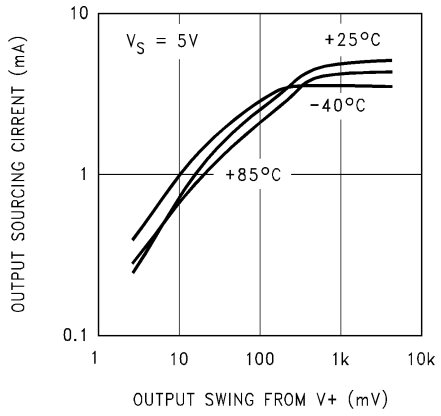


Figure 5-21. Output Voltage vs Sourcing Current

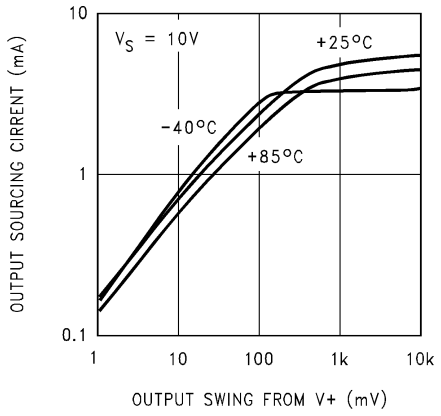


Figure 5-22. Output Voltage vs Sourcing Current

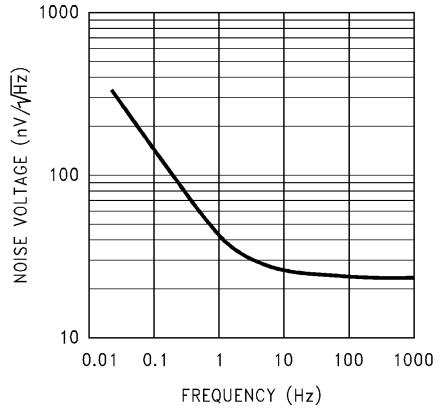


Figure 5-23. Noise Voltage vs Frequency

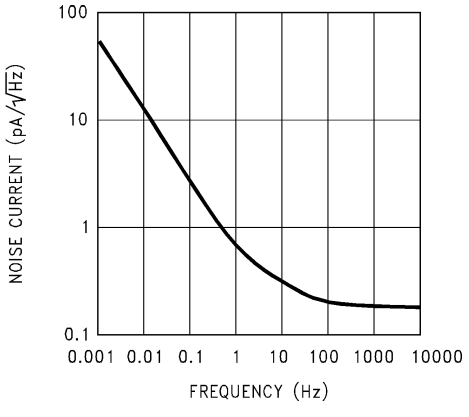


Figure 5-24. Noise Current vs Frequency

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5.9 Typical Characteristics (continued)

at T_A = 25°C and R_L = 10 kΩ (unless otherwise specified)

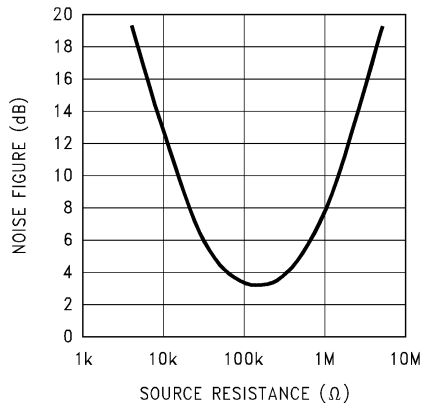


Figure 5-25. NF vs Source Resistance

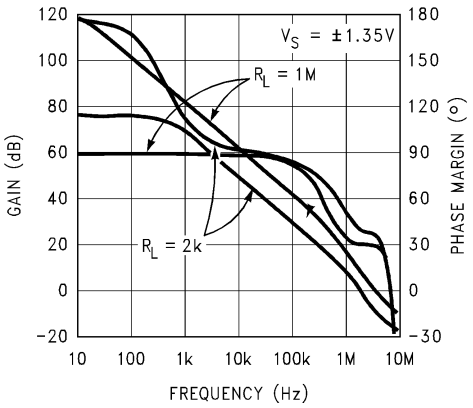


Figure 5-26. Gain and Phase vs Frequency, Old Die

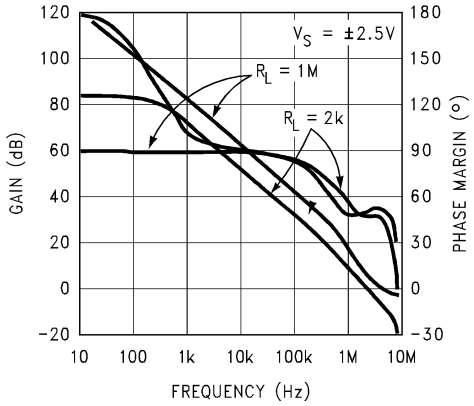


Figure 5-27. Gain and Phase vs Frequency, Old Die

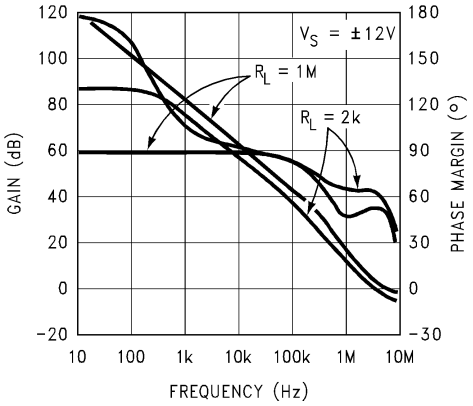


Figure 5-28. Gain and Phase vs Frequency, Old Die

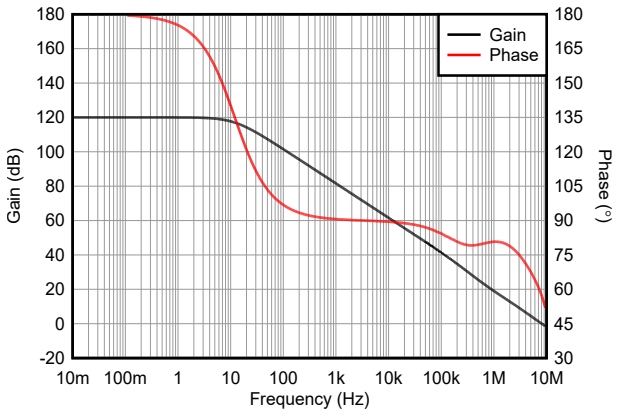


Figure 5-29. Gain and Phase vs Frequency, New Die

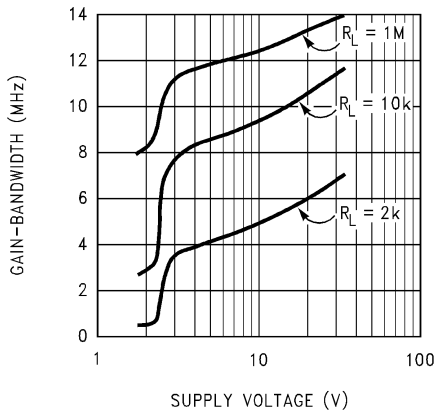


Figure 5-30. GBW vs Supply Voltage at 20 kHz

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5.10 Old Versus New Die Comparison

As of the publication of revision F of this data sheet, Texas Instruments has moved manufacturing of the die for LM6132 and LM6134 to a modern fabrication site. The two different die are referred to in this document as “old” (previous fabrication site) and “new” die. The die origin can be separated from the “Chip Source Origin” (CSO) parameter in the shipping information. The old die CSO is “GF6”, for the new die CSO is “RFB”. The old die information is maintained in this data sheet for comparison purposes, but all new manufacturing has moved to the new die.

Table 5-1. Old Versus New Die Comparison

Description	Old Die	New Die
Minimum supply voltage	1.8V	2.7V
Typical output voltage range for 100kΩ load (V_S = 5V)	0.007V - 4.992V	0.03V - 4.97V
Minimum output voltage range for 100kΩ load (V_S = 5V)	0.017V - 4.98V	0.04V - 4.965V
Output voltage slew architecture	Standard slew architecture	Slew-boosted architecture

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6 Application and Implementation

6.1 Application Information

The LM6132 brings a new level of ease of use to op amp system design. Greater than rail-to-rail input voltage eliminates concern over exceeding the common-mode voltage range.

Rail-to-rail output swing provides the maximum possible dynamic range at the output. This is particularly important when operating on low supply voltages.

The high gain-bandwidth with low supply current opens new battery powered applications, where high power consumption previously reduced battery life to unacceptable levels.

To take advantage of these features, keep some ideas in mind, which are outlined in subsequent sections.

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6.2 Typical Applications

6.2.1 Three Op Amp Instrumentation Amp with Rail-to-Rail Input and Output

Using the LM6134, a 3 op amp instrumentation amplifier with rail-to-rail inputs and rail to rail output can be made. These features make these instrumentation amplifiers an excellent choice for single supply systems.

Some manufacturers use a precision voltage divider array of 5 resistors to divide the common-mode voltage to get an input range of rail-to-rail or greater. The problem with this method is that the method also divides the signal, so to even get unity gain, the amplifier must be run at high closed loop gains. This raises the noise and drift by the internal gain factor and lowers the input impedance. Any mismatch in these precision resistors reduces the CMR as well. Using the LM6134, all of these problems are eliminated.

In this example, amplifiers A and B act as buffers to the differential stage (Figure 6-1). These buffers assure that the input impedance is over 100MΩ and they eliminate the requirement for precision matched resistors in the input stage. The buffers also assure that the difference amp is driven from a voltage source. This is necessary to maintain the CMR set by the matching of R1–R2 with R3–R4.

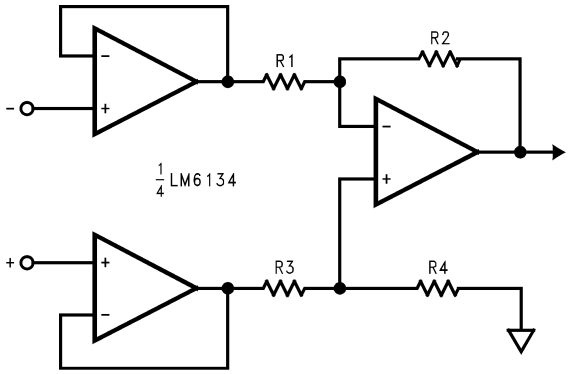


Figure 6-1. Instrumentation Amplifier

6.2.2 Flat Panel Display Buffering

Three features of the LM6132/34 make the device a superb choice for TFT LCD applications. First, the low current draw (360µA per amplifier at 5V) makes the device an excellent choice for battery powered applications such as in laptop computers. Second, since the device operates down to 2.7V, the device is a natural choice for next generation 3V TFT panels. Last, but not least, the large capacitive drive capability of the LM6132 comes in very handy in driving highly capacitive loads that are characteristic of LCD display drivers.

The large capacitive drive capability of the LM6132/34 allows the device to be used as buffers for the gamma correction reference voltage inputs of resistor-DAC type column (Source) drivers in TFT LCD panels. This amplifier is also useful for buffering only the center reference voltage input of Capacitor-DAC type column (Source) drivers such as the LMC750X series.

Since for VGA and SVGA displays, the buffered voltages must settle within approximately 4µs, the well known technique of using a small isolation resistor in series with the amplifier's output very effectively dampens the ringing at the output.

With the wide supply voltage range of 2.7V to 24V, the LM6132/34 can be used for a diverse range of applications. The system designer is thus able to select a single device type that serves many sub-circuits in the system, eliminating the need to specify multiple devices in the bill of materials. Along with the sister parts, the LM6142 and LM6152 that have the same wide supply voltage capability, choice of the LM6132 in a design eliminates the need to search for multiple sources for new designs.

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7 Device and Documentation Support

7.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

7.2 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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7.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.
All trademarks are the property of their respective owners.

7.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

7.5 Glossary

TI Glossary	This glossary lists and explains terms, acronyms, and definitions.

8 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision E (September 2014) to Revision F (June 2026)	Page
• Deleted "Swing 0.01V to 4.99V" in *Features*	1
• Deleted Supply Current vs. Supply Voltage plot	1
• Deleted Offset Voltage vs. Supply Voltage plot	1
• Added Functional Block Diagram	1
• Updated table note 3 in *Absolute Maximum Ratings*	4
• Changed from (V–) – 0.3V to (V–) – 0.5V	4
• Changed from (V+) + 0.3V to (V+) + 0.5V	4
• Updated table note 4 in *Absolute Maximum Ratings*	4
• Updated table note 2 in *Absolute Maximum Ratings*	4
• Changed from ±25mA to Continuous	4
• Changed rating from Current at Output Pin to Output short circuit	4
• Added Operating ambient temperature rating	4
• Added CDM ESD rating	4
• Updated table note in *ESD Ratings*	4
• Added table note in *ESD Ratings*	4
• Deleted table note 1 in *Recommended Operating Conditions*	4
• Changed minimum supply voltage from 1.8V to 2.7V	4
• Changed Junction-to-case thermal resistance for LM6132D from 193°C/W to 127.1°C/W	5
• Changed Junction-to-case thermal resistance for LM6132P from 115°C/W to 84.45°C/W	5
• Added Junction-to-case (top) thermal resistance for packages	5
• Added Junction-to-board thermal resistance for packages	5
• Added Junction-to-top characterization parameter for packages	5

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- Added Junction-to-board characterization parameter for packages....5
- Changed Junction-to-case thermal resistance for LM6134D from 126°C/W to 82.48°C/W....5
- Updated all *Electrical Characteristics* tables to latest format....6
- Updated Output Swing format to refer to rails....6
- Changed typical voltage output swing for 100kΩ load from 4.992V to 30mV from positive rail....6
- Changed maximum voltage output swing for 100kΩ load from 4.98V to 40mV from positive rail....6
- Changed typical voltage output swing for 100kΩ load from 0.007V to 30mV from negative rail....6
- Changed maximum voltage output swing for 100kΩ load from 0.017V to 35mV from negative rail....6
- Changed maximum voltage output swing for 100kΩ load over temperature from 0.019V to 50mV from negative rail....6
- Deleted table notes for all *Electric Characteristic* tables....6
- Updated Output Swing format to refer to rails....8
- Updated Output Swing format to refer to rails....9
- Added CMRR and PSRR vs Frequency plot for new die....10
- Added Gain and Phase vs Frequency plot for new die....10
- Added a new sub-section *Old Versus New Die Comparison*....15
- Deleted sub-section *Enhanced Slew Rate*....16

Changes from Revision D (February 2013) to Revision E (September 2014) **Page**

- Updated the numbering format for tables, figures, and cross-references throughout the document....0

Changes from Revision C (February 2013) to Revision D (February 2013) **Page**

- Changed layout of National Semicondutor Data Sheet to TI format....17

9 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
LM6132AIM/NOPB	Obsolete	Production	SOIC (D) | 8	-	-	Call TI	Call TI	-40 to 85	LM61 32AIM
LM6132AIMX/NOPB	Active	Production	SOIC (D) | 8	2500 | LARGE T&R	Yes	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 85	(LM61, M6132A) 32AIM
LM6132AIMX/NOPB.A	Active	Production	SOIC (D) | 8	2500 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(LM61, M6132A) 32AIM
LM6132AIMX/NOPB.B	Active	Production	SOIC (D) | 8	2500 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(LM61, M6132A) 32AIM
LM6132BIMX/NOPB	Active	Production	SOIC (D) | 8	2500 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 85	LM61 32BIM
LM6132BIMX/NOPB.A	Active	Production	SOIC (D) | 8	2500 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 85	LM61 32BIM
LM6132BIMX/NOPB.B	Active	Production	SOIC (D) | 8	2500 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 85	LM61 32BIM
LM6132BIN/NOPB	Active	Production	PDIP (P) | 8	40 | TUBE	Yes	NIPDAU	Level-1-NA-UNLIM	-40 to 85	(LM6132, LM6132BIN) BIN
LM6132BIN/NOPB.A	Active	Production	PDIP (P) | 8	40 | TUBE	Yes	NIPDAU	Level-1-NA-UNLIM	-40 to 85	(LM6132, LM6132BIN) BIN
LM6132BIN/NOPB.B	Active	Production	PDIP (P) | 8	40 | TUBE	Yes	NIPDAU	Level-1-NA-UNLIM	-40 to 85	(LM6132, LM6132BIN) BIN
LM6134AIM/NOPB	Obsolete	Production	SOIC (D) | 14	-	-	Call TI	Call TI	-40 to 85	LM6134AIM
LM6134AIMX/NOPB	Active	Production	SOIC (D) | 14	2500 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 85	LM6134AIM
LM6134AIMX/NOPB.A	Active	Production	SOIC (D) | 14	2500 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 85	LM6134AIM
LM6134BIM/NOPB	Obsolete	Production	SOIC (D) | 14	-	-	Call TI	Call TI	-40 to 85	LM6134BIM
LM6134BIMX/NOPB	Active	Production	SOIC (D) | 14	2500 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 85	LM6134BIM
LM6134BIMX/NOPB.A	Active	Production	SOIC (D) | 14	2500 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 85	LM6134BIM
LM6134BIN/NOPB	Active	Production	PDIP (N) | 14	25 | TUBE	Yes	NIPDAU	Level-1-NA-UNLIM	-40 to 85	LM6134BIN
LM6134BIN/NOPB.A	Active	Production	PDIP (N) | 14	25 | TUBE	Yes	NIPDAU	Level-1-NA-UNLIM	-40 to 85	LM6134BIN

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

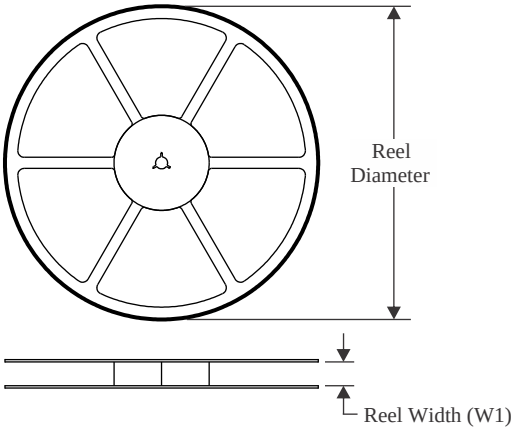
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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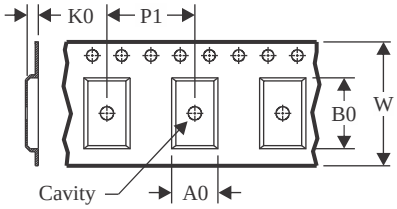
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

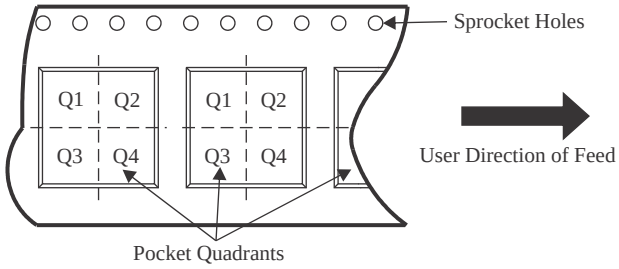


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

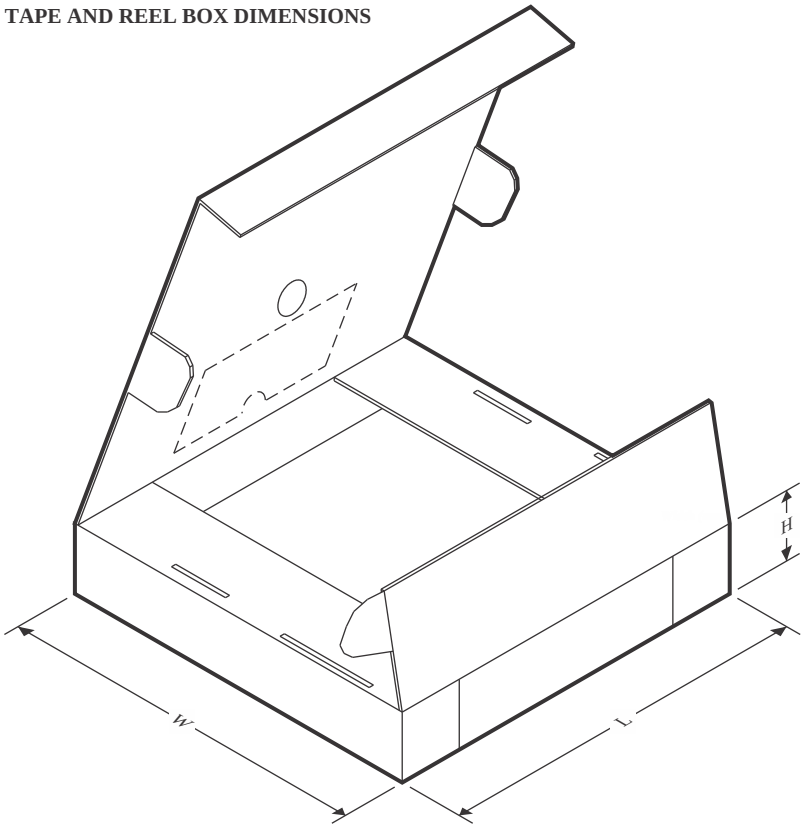
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LM6132AIMX/NOPB	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM6132BIMX/NOPB	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LM6134AIMX/NOPB	SOIC	D	14	2500	330.0	16.4	6.5	9.35	2.3	8.0	16.0	Q1
LM6134BIMX/NOPB	SOIC	D	14	2500	330.0	16.4	6.5	9.35	2.3	8.0	16.0	Q1

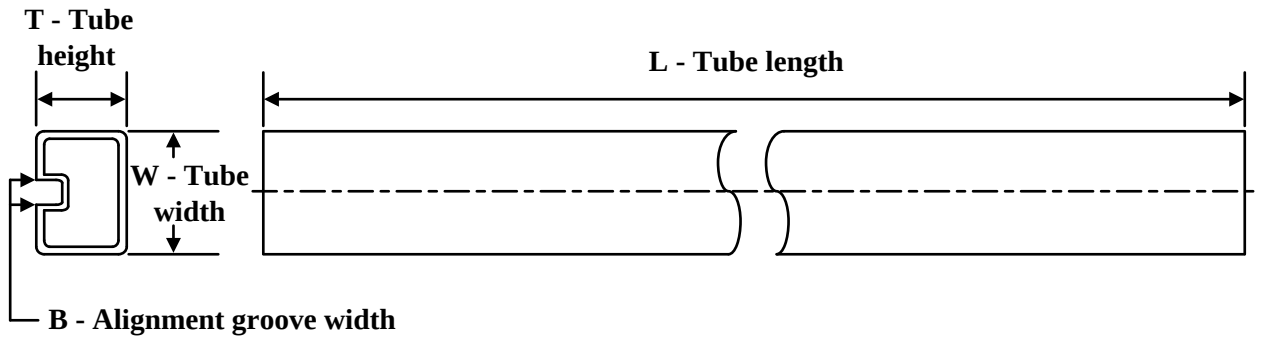
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

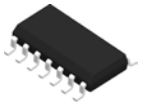
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LM6132AIMX/NOPB	SOIC	D	8	2500	367.0	367.0	35.0
LM6132BIMX/NOPB	SOIC	D	8	2500	367.0	367.0	35.0
LM6134AIMX/NOPB	SOIC	D	14	2500	367.0	367.0	35.0
LM6134BIMX/NOPB	SOIC	D	14	2500	367.0	367.0	35.0

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
LM6132BIN/NOPB	P	PDIP	8	40	506	13.97	11230	4.32
LM6132BIN/NOPB	P	PDIP	8	40	502	14	11938	4.32
LM6132BIN/NOPB.A	P	PDIP	8	40	506	13.97	11230	4.32
LM6132BIN/NOPB.A	P	PDIP	8	40	502	14	11938	4.32
LM6132BIN/NOPB.B	P	PDIP	8	40	502	14	11938	4.32
LM6132BIN/NOPB.B	P	PDIP	8	40	506	13.97	11230	4.32
LM6134BIN/NOPB	N	PDIP	14	25	502	14	11938	4.32
LM6134BIN/NOPB.A	N	PDIP	14	25	502	14	11938	4.32

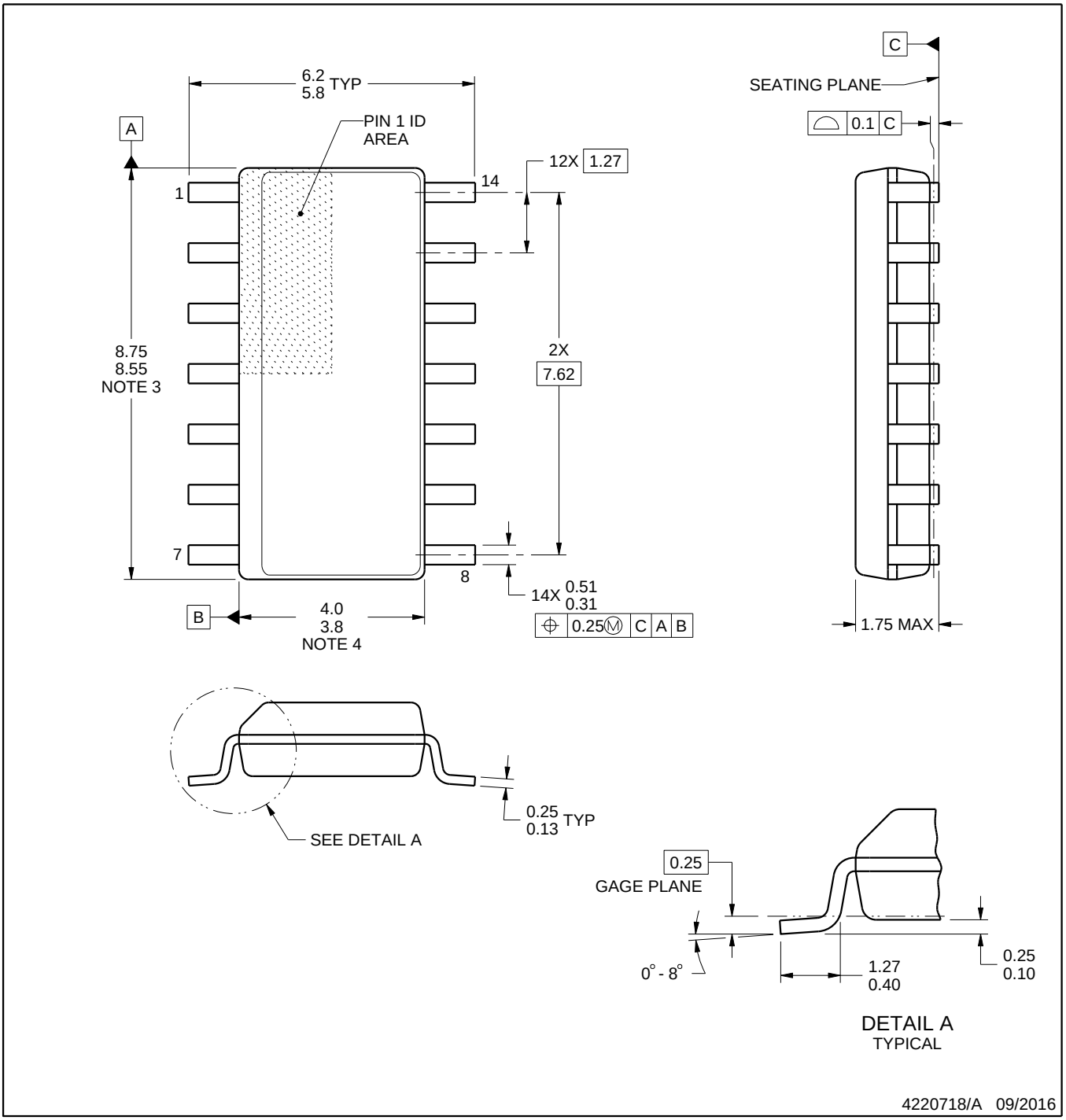


PACKAGE OUTLINE

D0014A

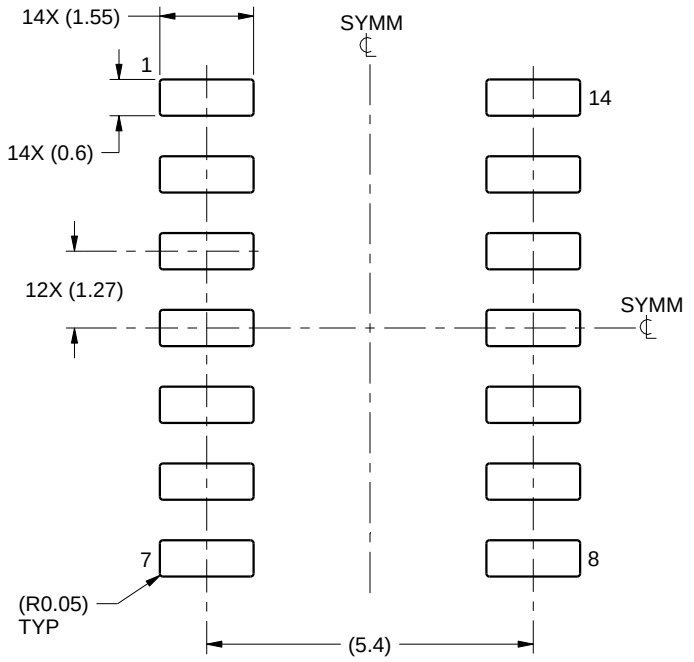
SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

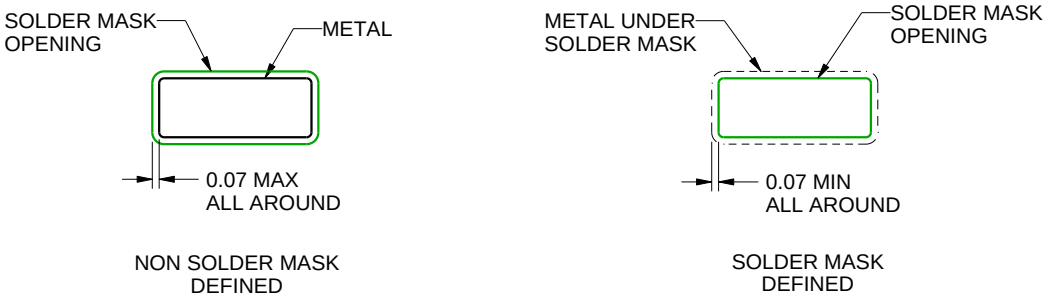


NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
5. Reference JEDEC registration MS-012, variation AB.



LAND PATTERN EXAMPLE
SCALE:8X



SOLDER MASK DETAILS

4220718/A 09/2016

NOTES: (continued)

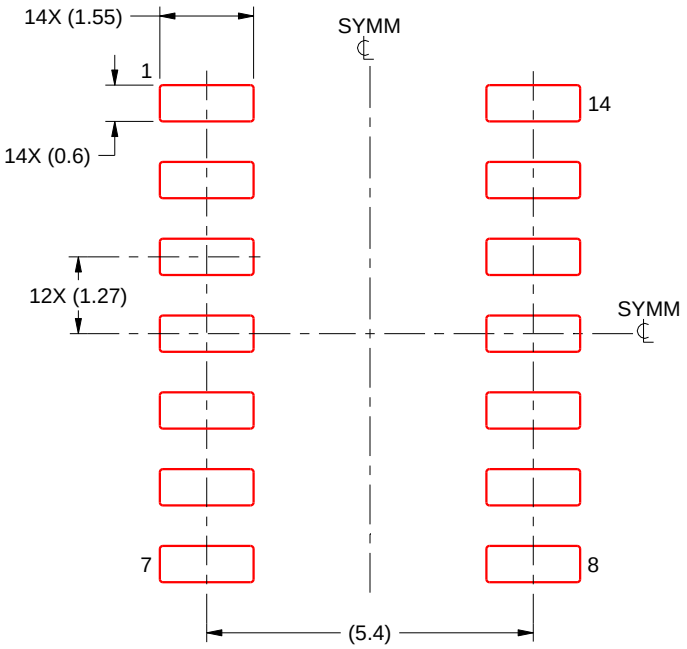
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

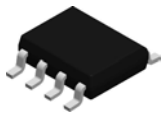


SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:8X

4220718/A 09/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

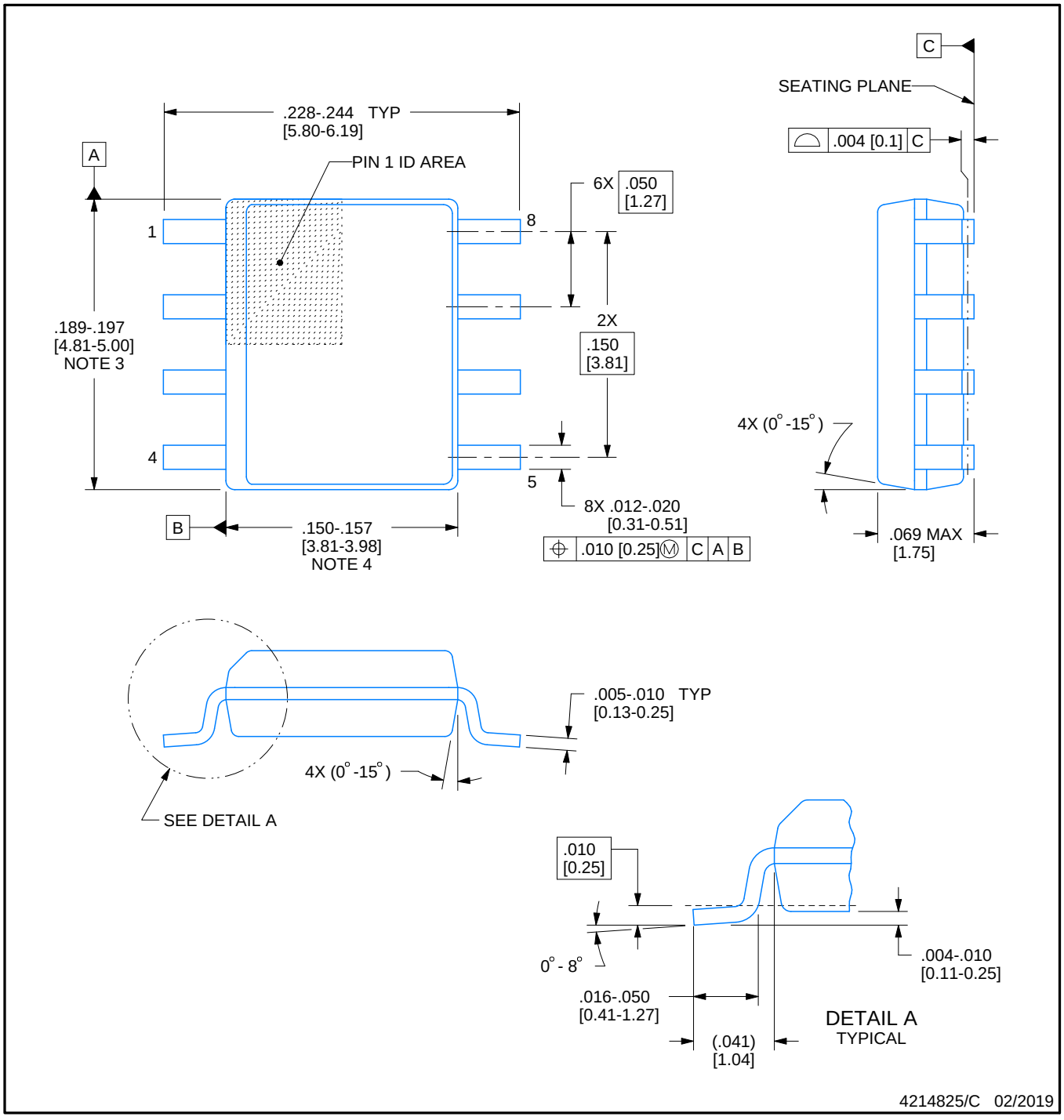


PACKAGE OUTLINE

D0008A

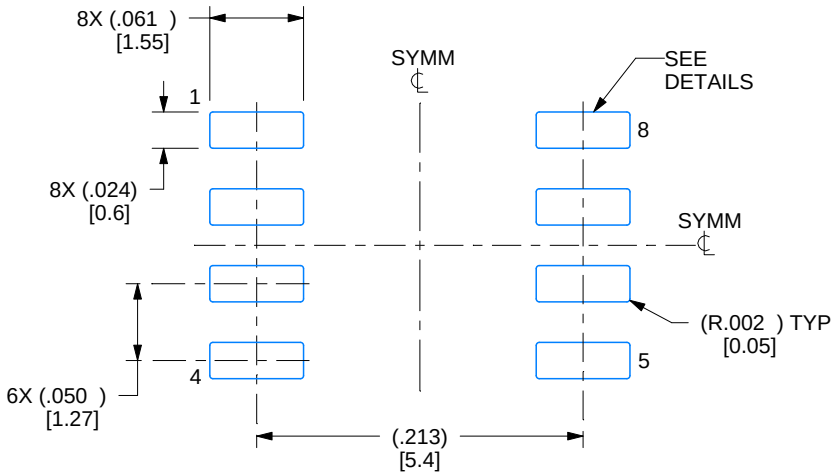
SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

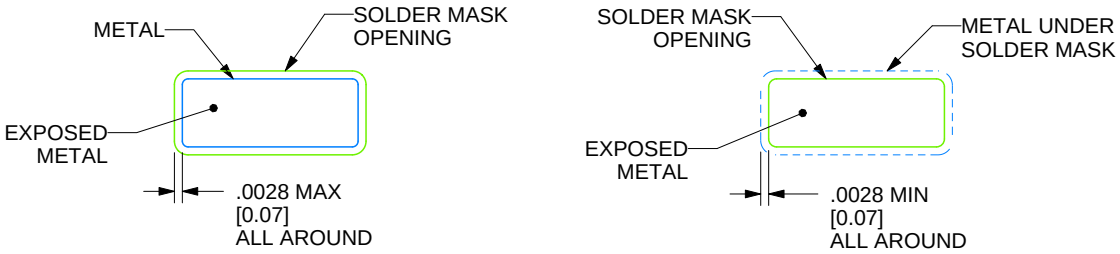


NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

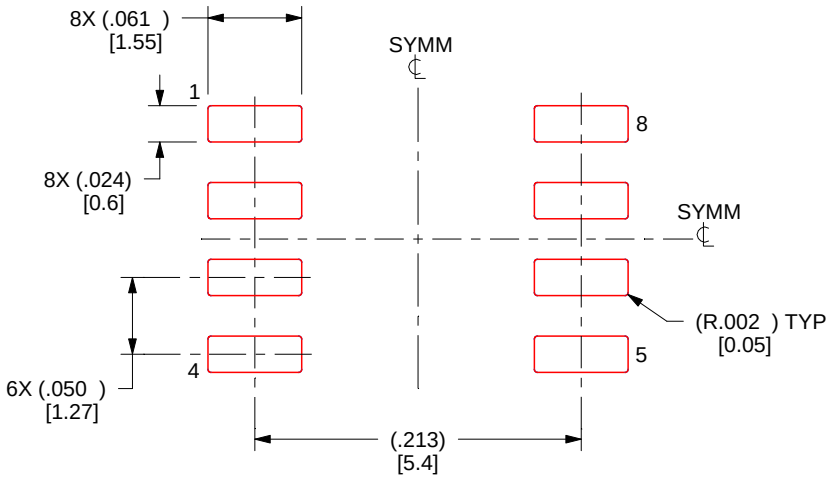
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



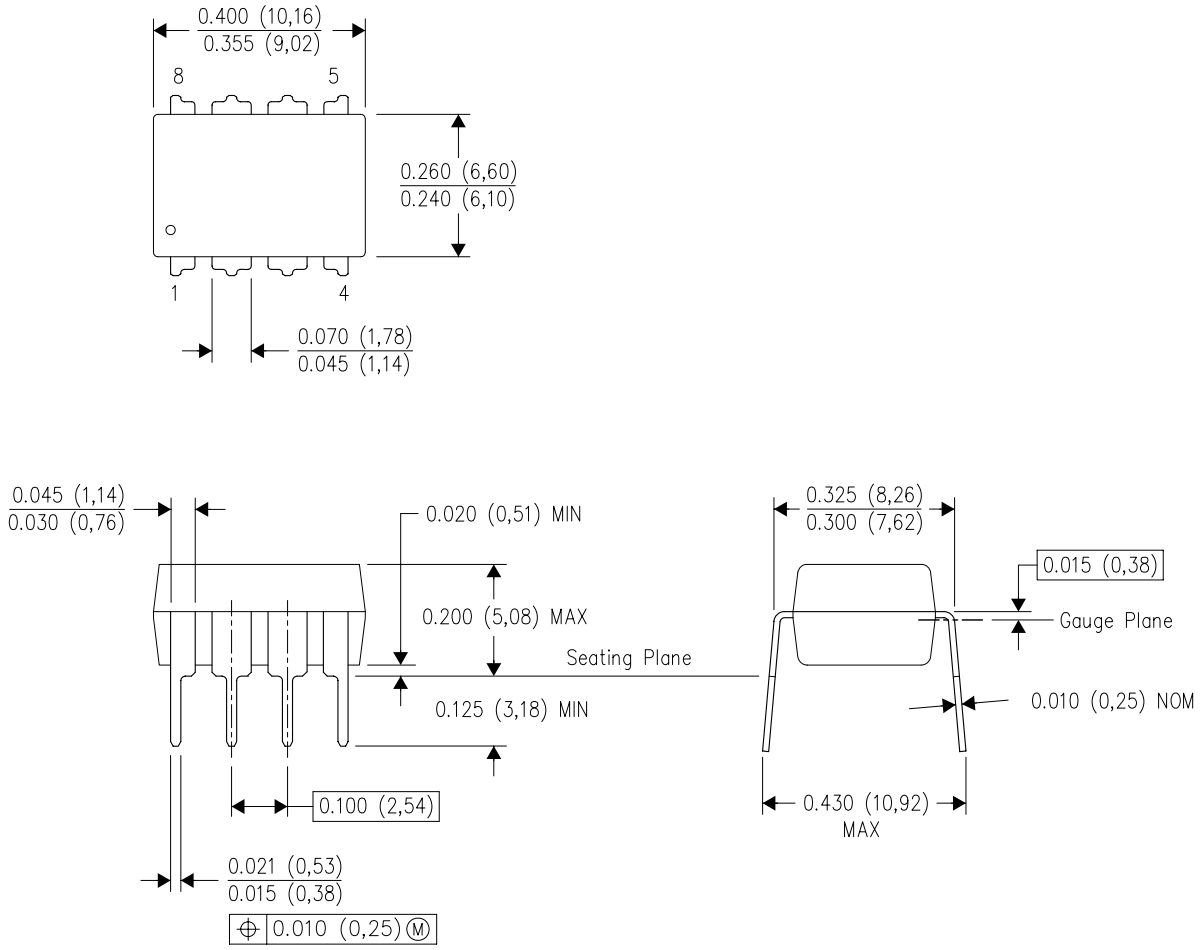
SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

P (R–PDIP–T8) PLASTIC DUAL–IN–LINE PACKAGE

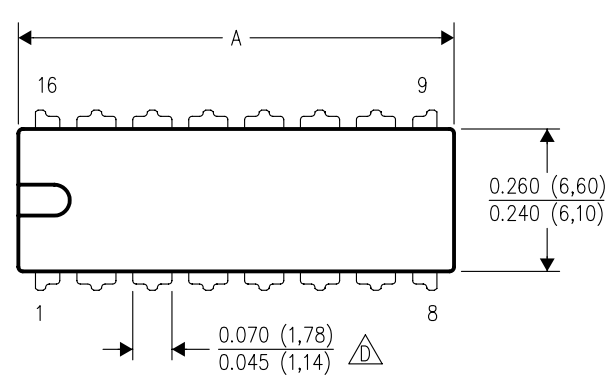


NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Falls within JEDEC MS–001 variation BA.

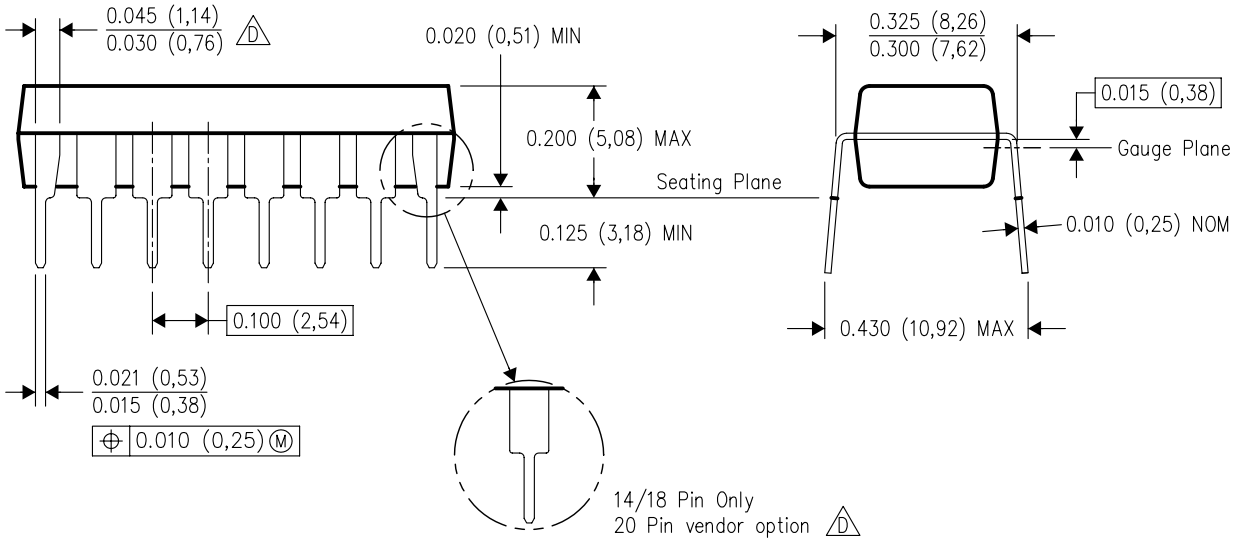
N (R–PDIP–T**)

PLASTIC DUAL–IN–LINE PACKAGE

16 PINS SHOWN



DIM \ PINS **	14	16	18	20
A MAX	0.775 (19,69)	0.775 (19,69)	0.920 (23,37)	1.060 (26,92)
A MIN	0.745 (18,92)	0.745 (18,92)	0.850 (21,59)	0.940 (23,88)
MS–001 VARIATION (C)	AA	BB	AC	AD



4040049/E 12/2002

NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Falls within JEDEC MS–001, except 18 and 20 pin minimum body length (Dim A).
D. The 20 pin end lead shoulder width is a vendor option, either half or full width.

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